SLIM, Short-pulse Technology for High Gradient Induction Accelerators

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Outline

- Accelerating Gradient in Induction Linacs

- Analyze Ways How to Increase Gradient

- High Gradient Induction Cells Based on Solid State Approaches (DWAs)

- SLIM: *SL*AC *I*nduction *M*odule (or *M*ethod)

- SLIM Embodiment

- Comparison of DWA and SLIM

- Some Advantages with Development of the SLIM-based Concept

- Conclusion

Accelerating Gradient in Induction Linacs
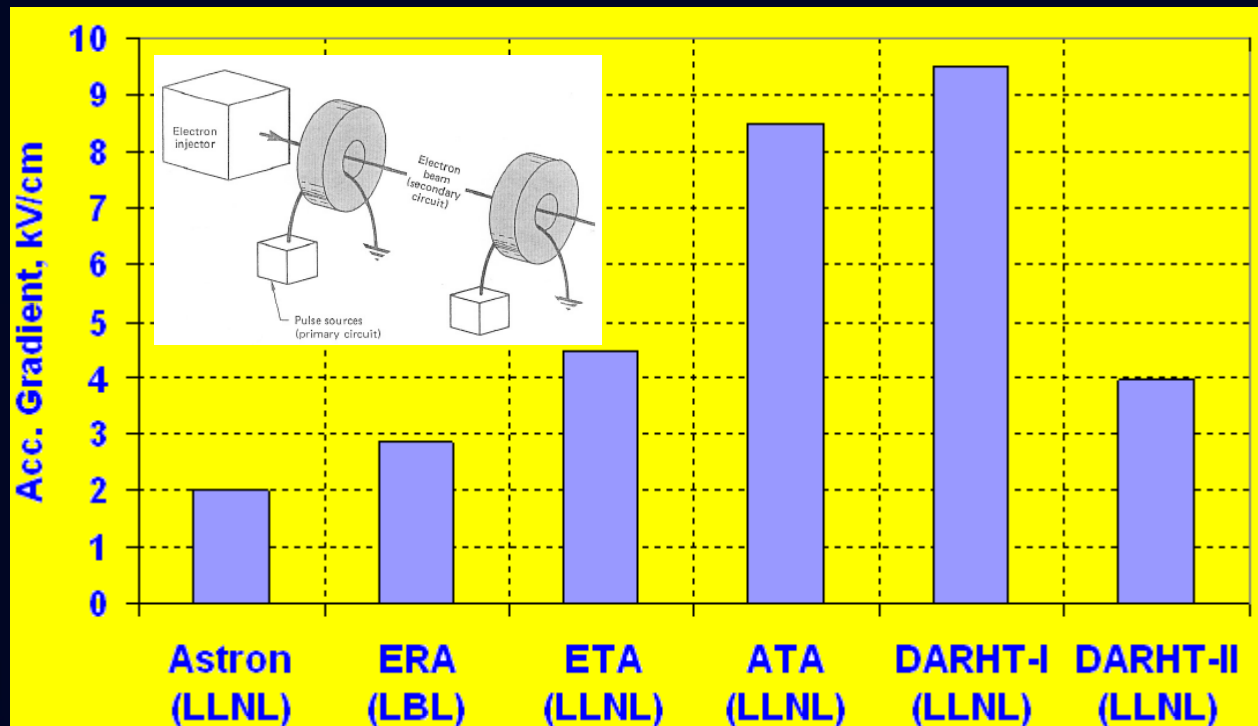
The machines were build in the period 1963-2003 (i.e. the 40 years progress)
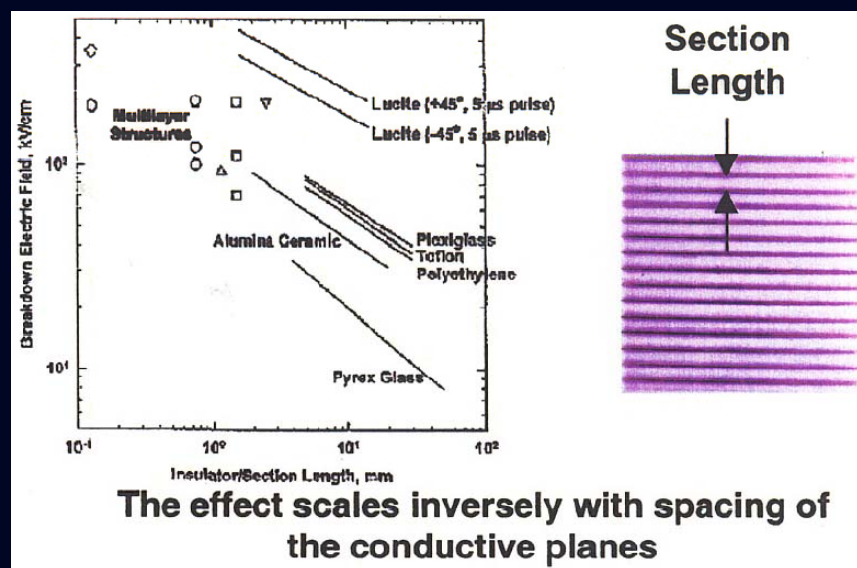
Machines in other countries (France, Russia, China, etc.) have similar accelerating gradient

Analyze Ways How to Increase Gradient

There are two natural ways to increase the acc. gradient
• a reduction of the pulse width
• a reduction of the section length

$$E_{gain} \propto \sqrt[3]{\frac{t_{1u\,sec}}{t_p}}$$
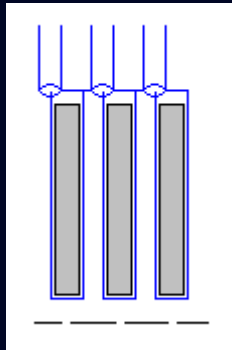

The effect scales inversely with spacing of the conductive planes

Culled from the published articles

Can the classical induction system deal with pulse widths in the nsec range?

There is the same V*sec integral

but the core does not react in the same manner

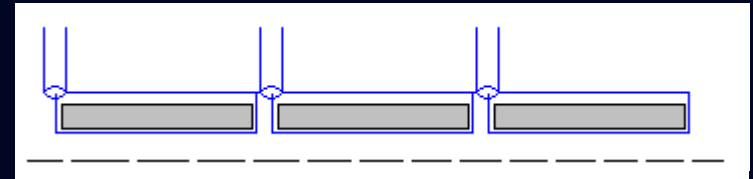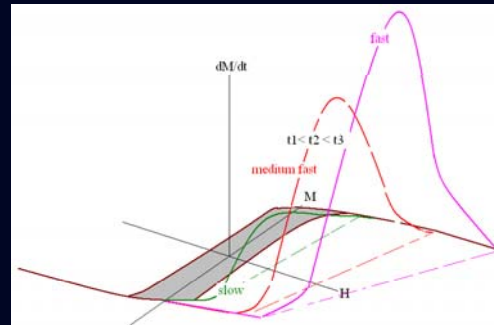$$\frac{dm}{dt} = \frac{\lambda}{M_s} \cdot H(t) \cdot [1 - m(t)^2]$$
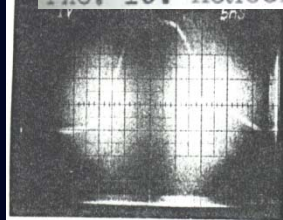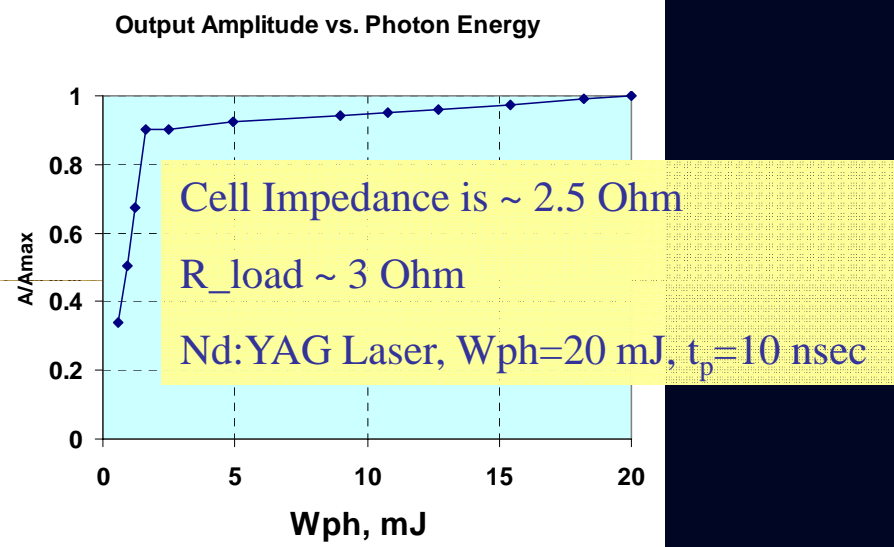
$$m = \frac{M(t)}{M_s}$$

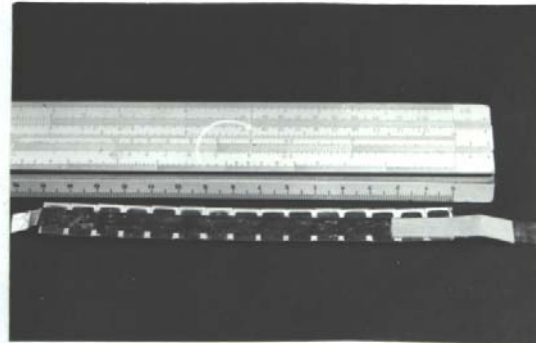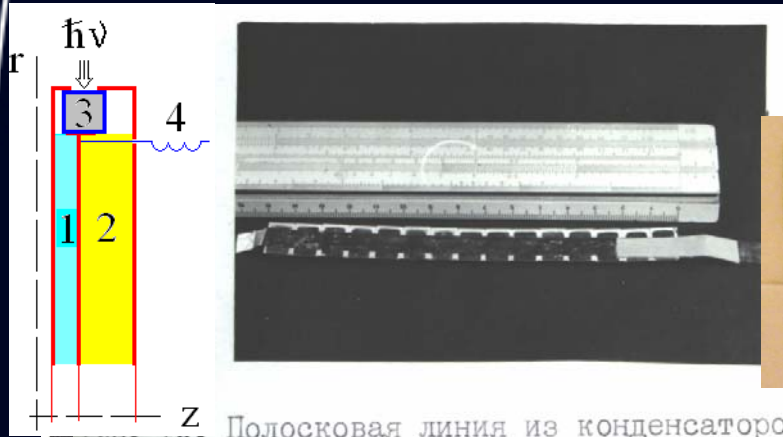A dynamic of magnetization is fast

(short accelerating pulses are possible)

A dynamic of magnetization is slow

(long accelerating pulse widths)
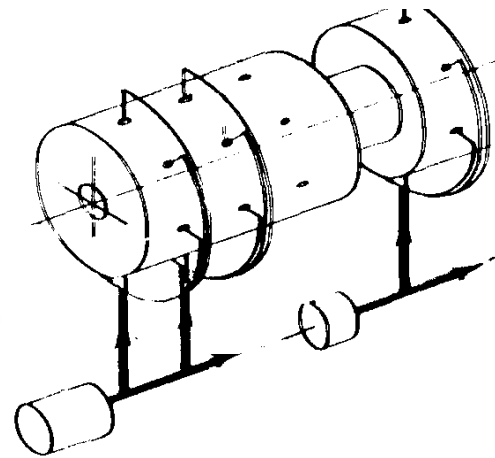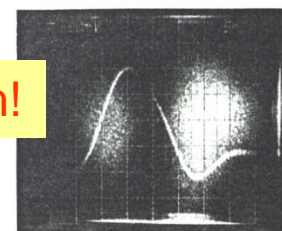
$$r(m) = \frac{dm(t)}{dQ} M_s$$

This is a core parameter for the effectiveness of driven accelerating gap (it is similar to the "shunt impedance" in the rf engineering)

The induction system that has a large core ratio OD/ID, will not work effectively in nsec range. The power supply energy goes to the core instead of to the beam.

High Gradient Induction Cells Based on Solid State Approaches (our DWAs in the '80s)

$\hbar\nu$

Полосковая линия из конденсаторо

Output Amplitude vs. Photon Energy

Cell Impedance is ~ 2.5 Ohm

R_load ~ 3 Ohm

Nd:YAG Laser, Wph=20 mJ, t_p=10 nsec

$E \simeq 10 \frac{\kappa B}{cm}$; б)

$E \simeq 20 \frac{\kappa B}{cm}$ в)

$E \simeq 50 \frac{\kappa B}{cm}$; г)

д)
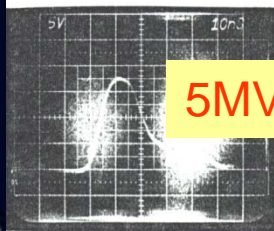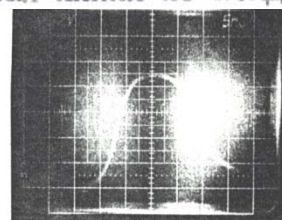
5MV/m!

$$\frac{W_{\hbar\nu}}{W_{ind}} \cong 10^{-3}$$

$$t_{ch} \gg t_p$$

$$E_z^p \leq E_z^{ch}$$

Recent Result from the LLNL Team
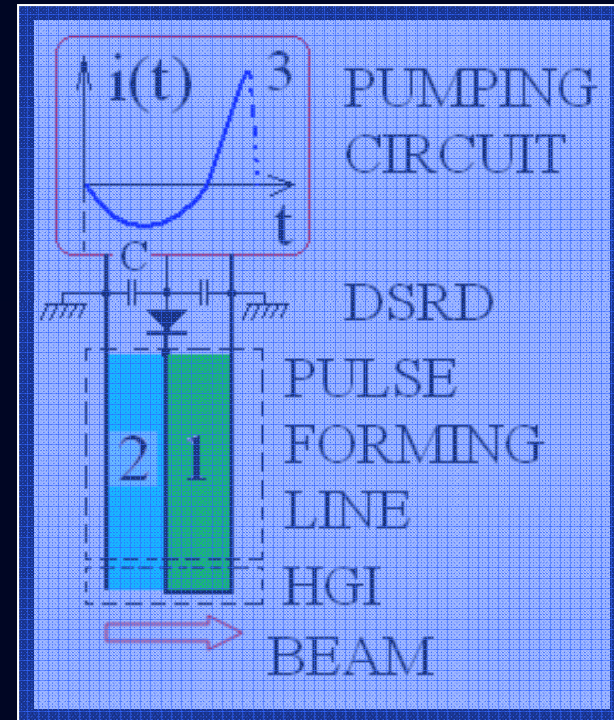## (Courtesy of G. Caporaso)
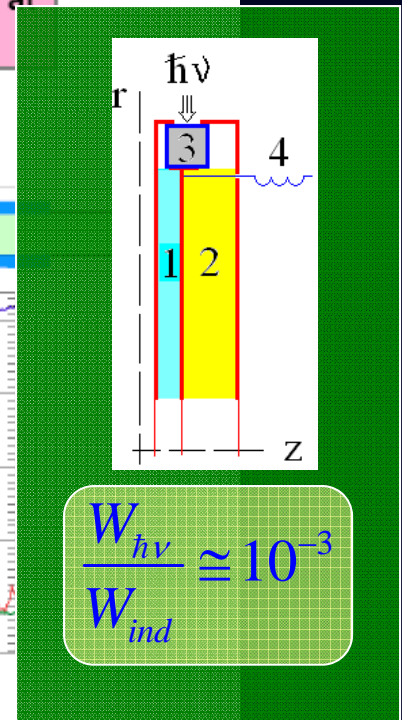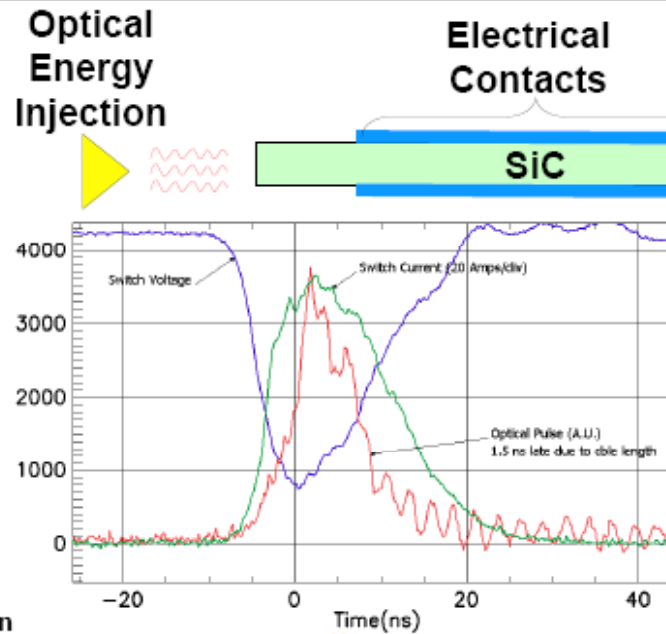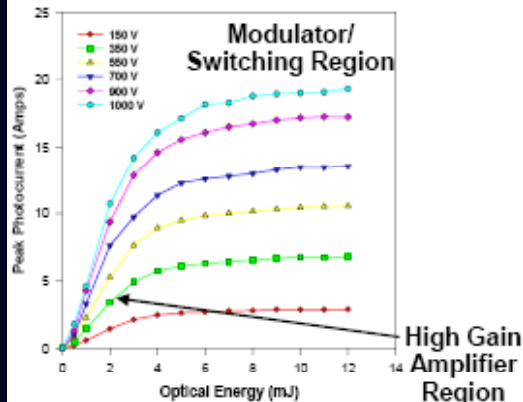
SLIM: *SL*AC *I*nduction *M*odule (or *M*ethod)

- SLIM employs the coreless induction linac concept
- SLIM is based on the nsec TEM pulse mode operation with no laser or RF systems
- The SLIM induction system produces the "traveling mono-pulse" of the electric field that propagates in synchronism with the accelerating beam (like the DWA concept)
- The induction system of SLIM contains three components; an opening switch (a Drift Step Recovery Diode), an inductive energy storage, and a sleeve (solid-to-vacuum interface)
- Advanced solid state semiconductor technology and modern microfabrication techniques are used in the SLIM concept

SLIM Embodiment
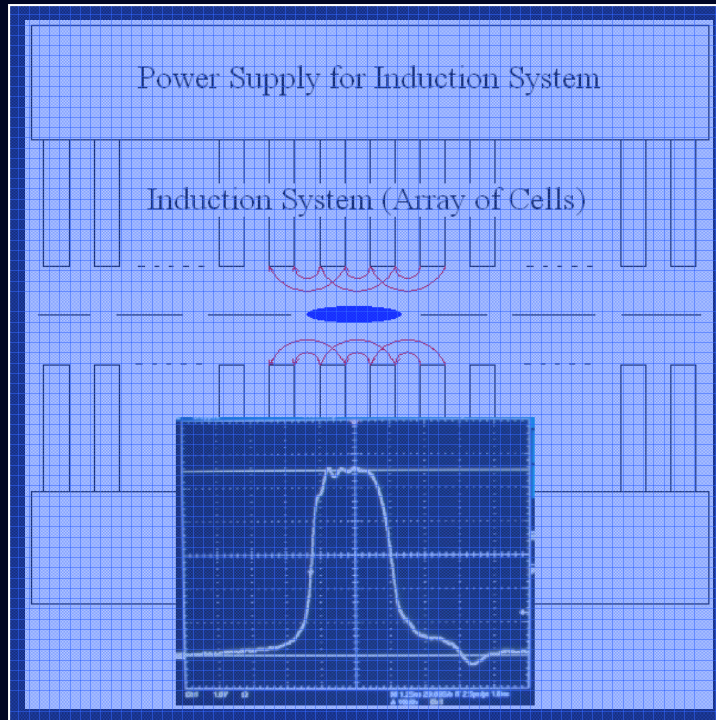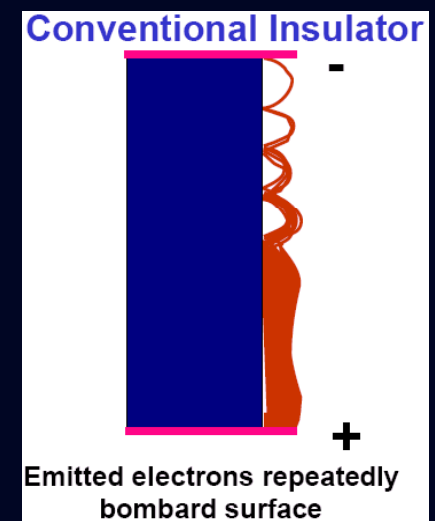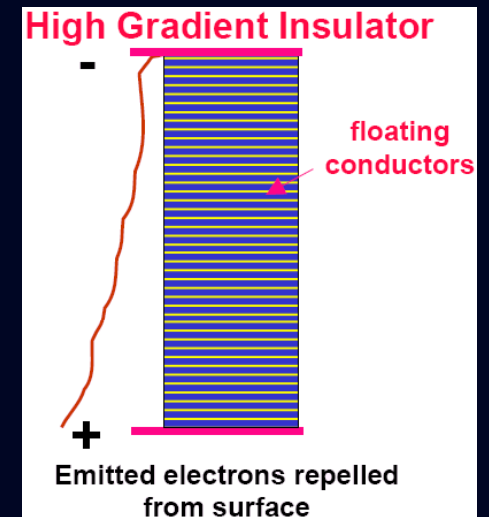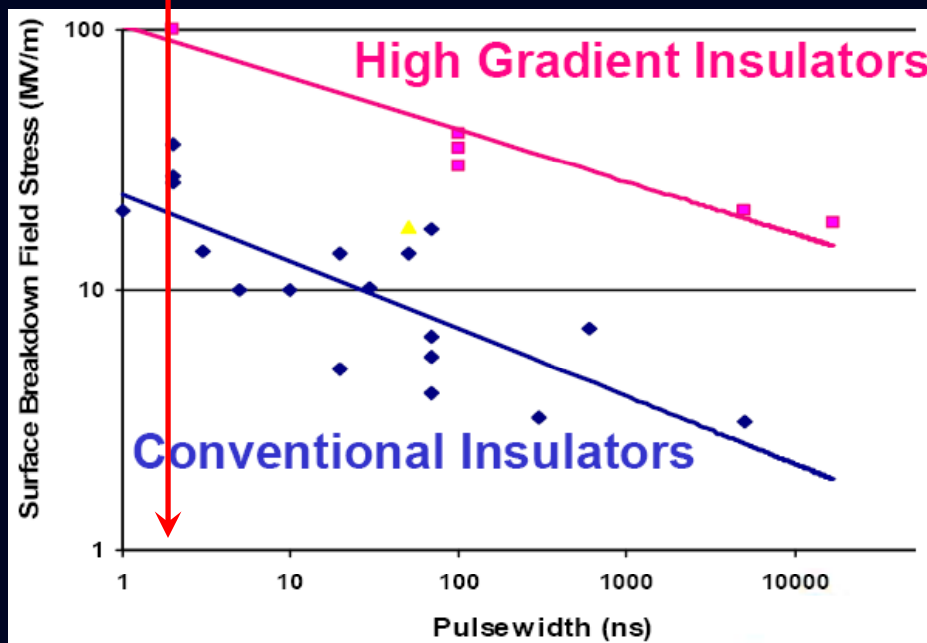

A presence of 100 MV/m field in the cell is only for 2 nsec. The rest of time the DSRD switch keeps gradient at zero level.

Main SLIM components: HGI

Range of a Pulse Width is (1-4) ns

High Gradient Insulator

floating conductors

Emitted electrons repelled from surface

Conventional Insulator

Emitted electrons repeatedly bombard surface

Courtesy of George Caporaso, LLNL

Main SLIM components: DSRD

20 ns/div
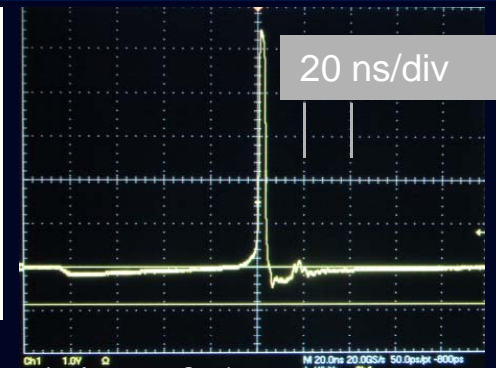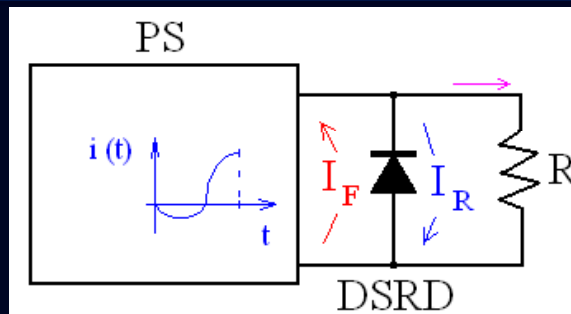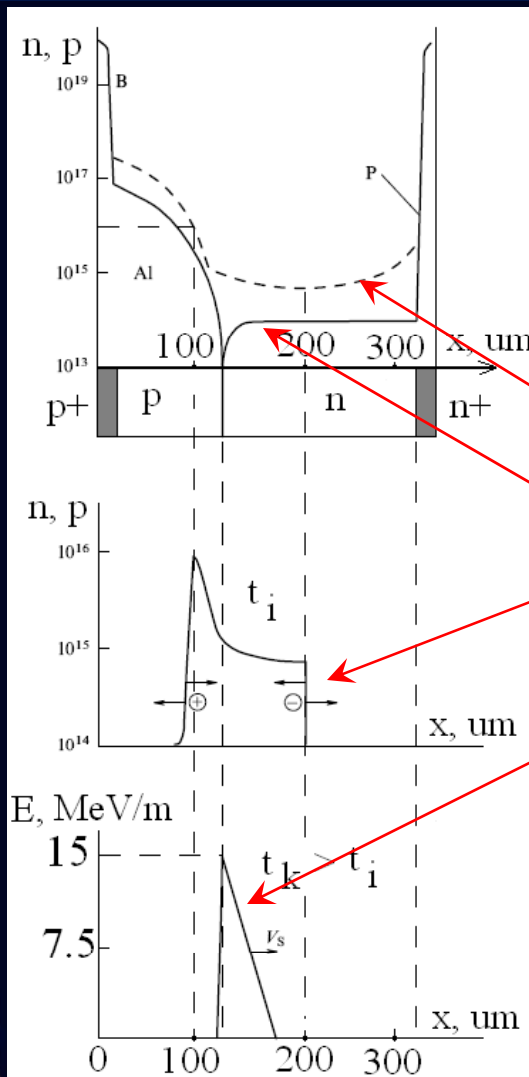
A plasma distribution after applying of short forward current

A profile of dopant concentration

Two plasma fronts are moving fast ($v=10^7$ cm/sec) to each other toward to the p-n junction.

When both fronts are collided the Space Charge Region is formed.

The reverse current is abrupt in the DSRD and it jumps to the load.

The voltage on the load is erected quickly. The stored energy starts to be delivered to the load.

More Details of the SLIM Embodiment
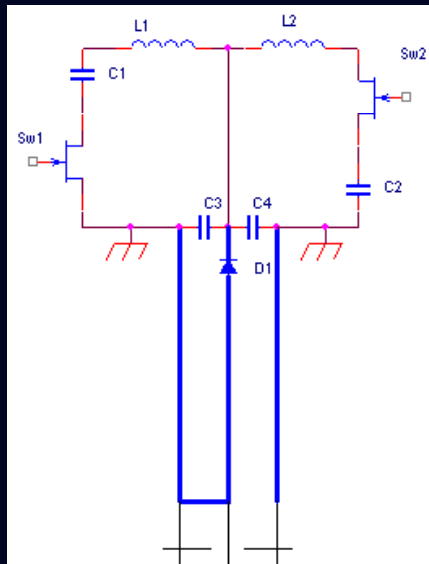
A simplified circuit to pump of the SLIM cell

A variant of the SLIM cell with the integrated DSRD opening switch

5 ns/div

High Accelerating Gradient depends on the di/dt rate in DSRD

100 MeV/m ⟹ di/dt ~ 4 kA/ns

DWA vs. SLIM (comparison)

A cell dielectric is stressed during charging cycle.

There is an erected voltage on the outer side of an induction system during the delivery of energy.

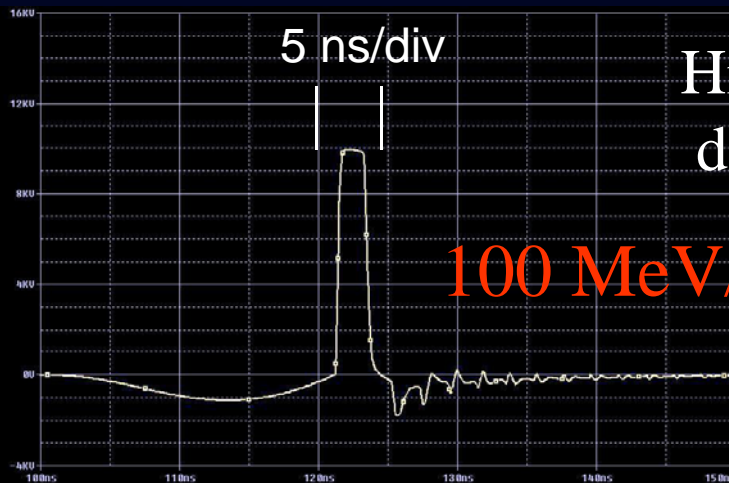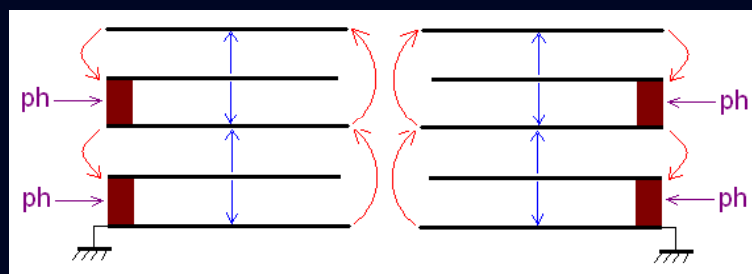A stressed turn ON solid state switch is employed in a cell.

A cell switch is controlled by a low efficient manner. A laser system is used.

A high electric field in cell persists a long period of time.
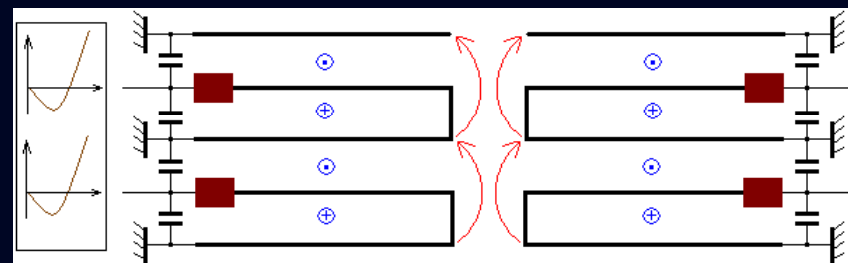
A cell dielectric is NOT stressed during charging cycle.

An outer side cell voltage is zero. Cells are not floated.

A solid state OFF switch is employed in a cell.

A cell switch is controlled by an electrical manner. No laser system is required.

A high electric field in cell persists during the pulse width only.

Some Advantages with Developing
of the SLIM-based Concept

• In the USA a 4 GeV, 10 kA, 10 ns, 6 PPS Induction Linac for Heavy Ion Fusion Program is based on 1.5 MeV/m gradient.

The SLIM-based concept may bring a new impulse for a development in this national program

Some Advantages with Developing of the SLIM-based Concept (cont.)

- Hadron synchrotron RF cavities (for example, for the LHC upgrade) will require the gain of 3 MeV/turn for a 25 A peak current and a pulse width of 500 ns (super bunch operation mode).
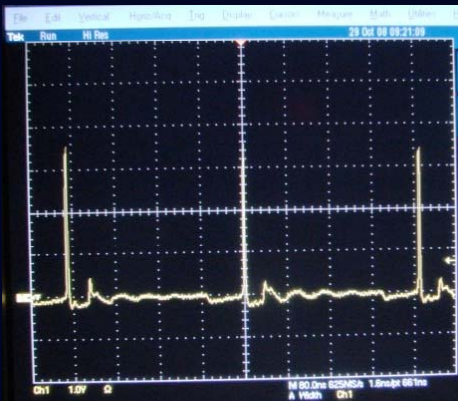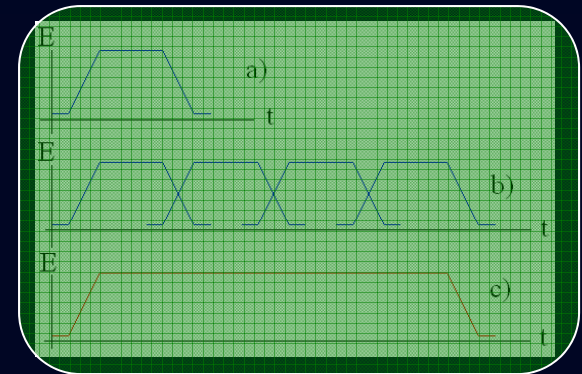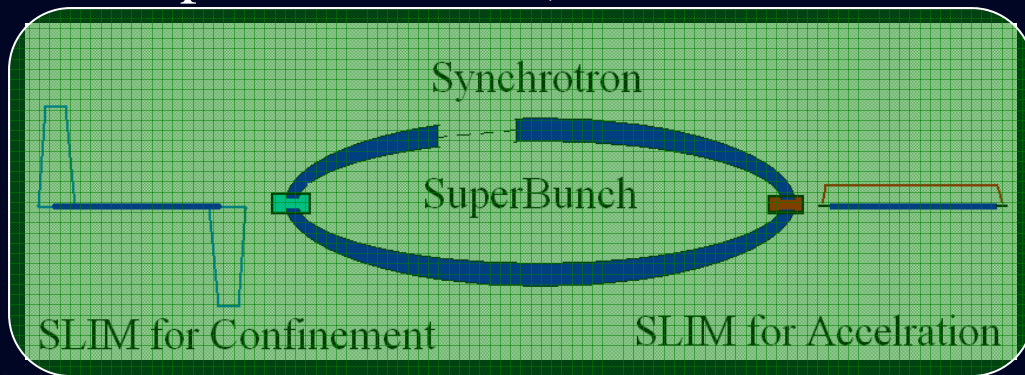
There are possibilities of

- A fast control of the spatial $E(z,t)$ distribution along SLIM cells

- A 3MHz mode operation

Some Advantages with Developing of the SLIM-based Concept (cont.)

- A modulation of the solid state plasma in the SLIM concept is produced by the gradient of a doping concentration and the pumping of the p-n junction by the pulse current (in forward and reverse directions). The array of lined up and activated DSRD may be a potential structure for the advanced accelerating technology
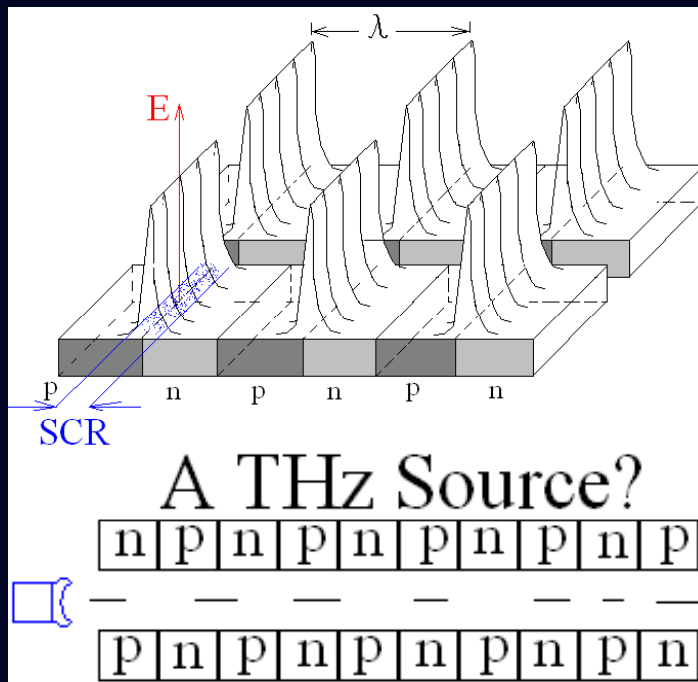
For example,

$$E \cong 15 \frac{MeV}{m}$$

$$\lambda_w \simeq 200 \, \mu m$$

a strong B_z is acceptable

Some Advantages with Development of the SLIM-based Concept (cont.)

SLIM mode operation vs. RF resonance mode

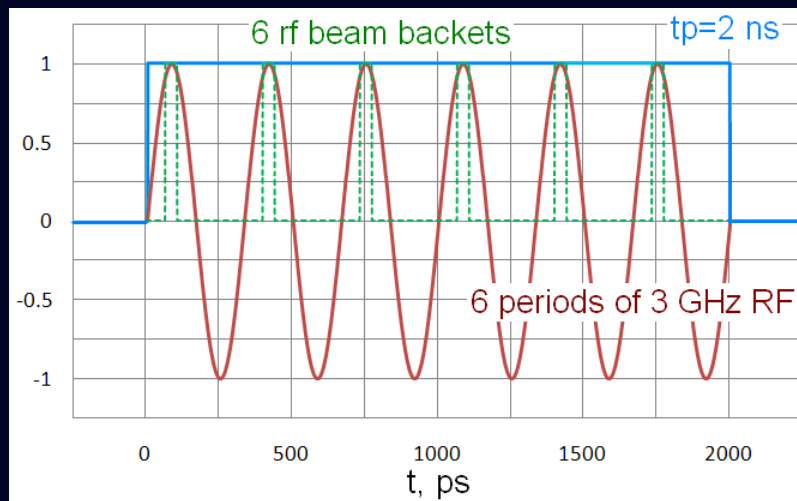
- Intensity:

$$Gain \cong \frac{2\pi}{\varphi_b} \sim 8$$

- TEM mode operation (with no RF filling time)

Conclusion

- The gradient of the SLIM-based technology is believed to be achievable in the same range as it is for the gradient of a modern rf-linac technology (~100 MeV per meter)

- The SLIM concept is based on the nsec TEM pulse mode operation with no laser or rf systems

- Main components of SLIM are not stressed while the energy is pumped into the induction system. Components can accept the hard environment conditions such as a radiation dose, mismatch, hard electromagnetic nose level, etc. Only for several nanoseconds the switch is OFF and produces a stress in the induction system. At that time, the delivery of energy to the beam takes place

Conclusion (cont.)

- The energy in the induction system initially is storied in the magnetic field when the switch is ON. That fact makes another benefit: a low voltage power supplies can be used. The reliability of a lower voltage power supply is higher and they are cheaper

- The coreless SLIM concept offers to work in the MHz range of repetition rate. The induction system has the high electric efficiency (much higher than the DWA)

- The array of lined up and activated SLIM cells is believed to be a solid state structure of novel accelerating technology. The electron-hole plasma in the high power solid state structure is precisely controlled by the electromagnetic process of a pulsed power supply

Acknowledgement

- Authors would like to thank you for your attention

- The pioneering high gradient study for the induction method of acceleration was performed in the Prof. Sarantsev Dept. in 80's (JINR, Dubna)